



### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.4	0.7	1	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance <small>note2</small>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	-	21	27	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3A	-	29	44	
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHz	-	358	-	pF
C <sub>oss</sub>	Output Capacitance		-	69.3	-	pF
C <sub>riss</sub>	Reverse Transfer Capacitance		-	58.5	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =10V, I <sub>D</sub> =2A, V <sub>GS</sub> =4.5V	-	5.6	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	0.8	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	1	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =10V, I <sub>D</sub> =4A, R <sub>GEN</sub> =3Ω, V <sub>GS</sub> =4.5V	-	5	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	30	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	48	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	36	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	4	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =4A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure 1: Output Characteristics

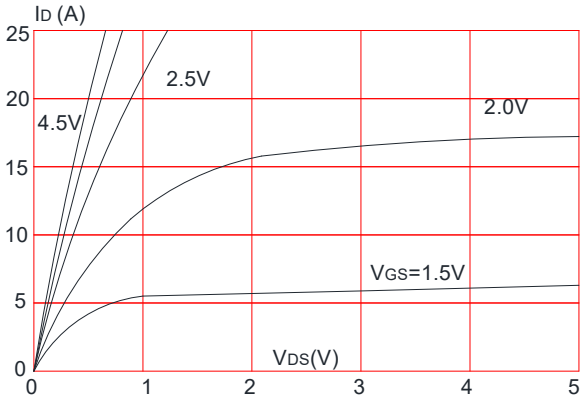


Figure 2: Typical Transfer Characteristics

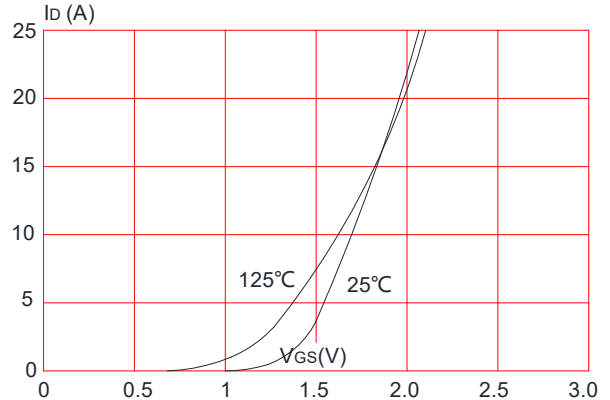


Figure 3: On-resistance vs. Drain Current

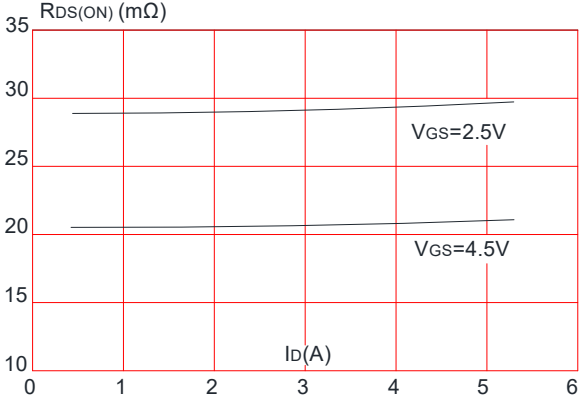


Figure 4: Body Diode Characteristics

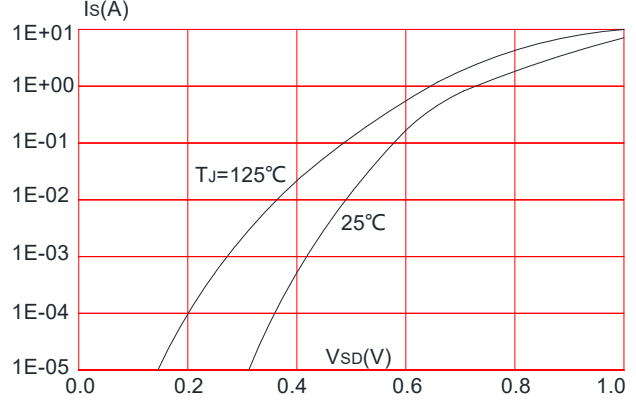


Figure 5: Gate Charge Characteristics

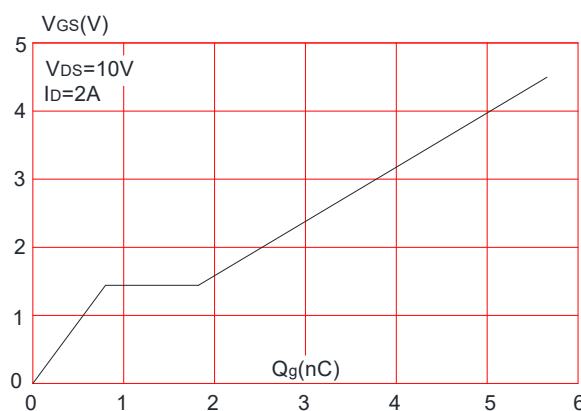
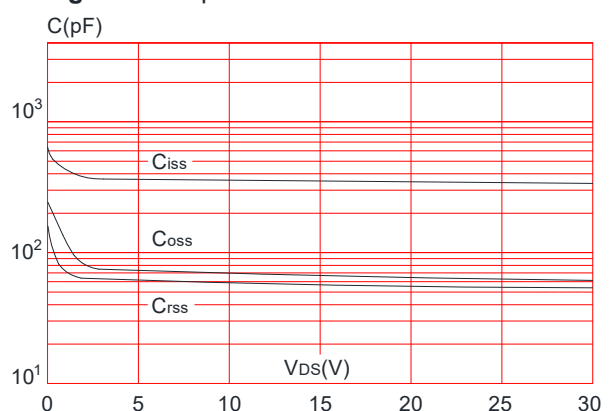
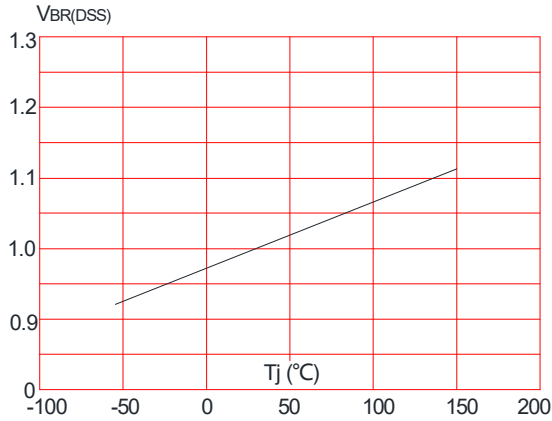


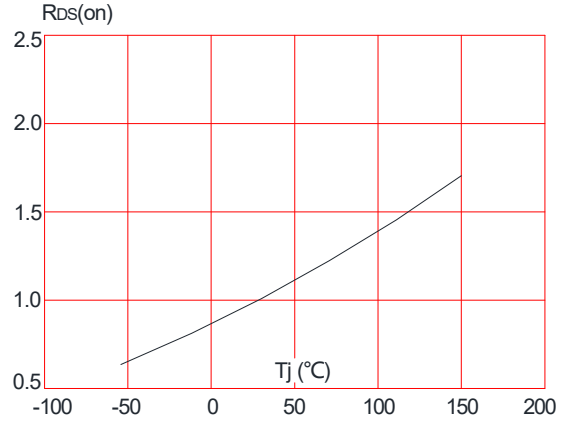
Figure 6: Capacitance Characteristics



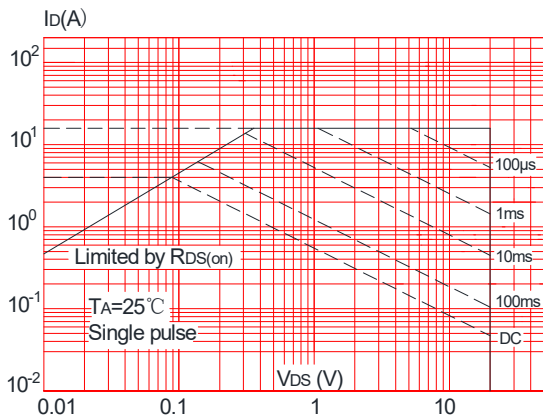
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



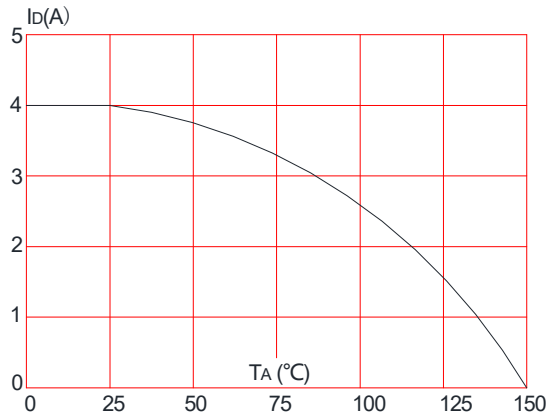
**Figure 8:** Normalized on Resistance vs. Junction Temperature



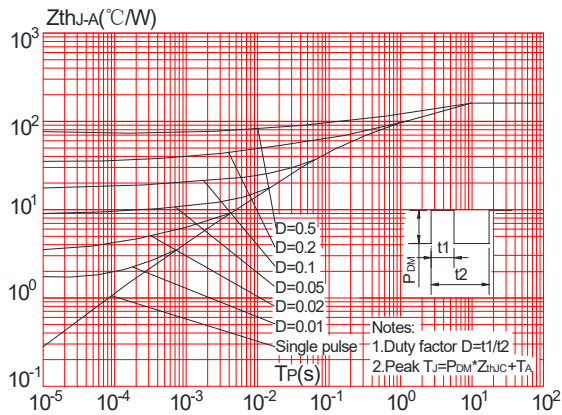
**Figure 9:** Maximum Safe Operating Area



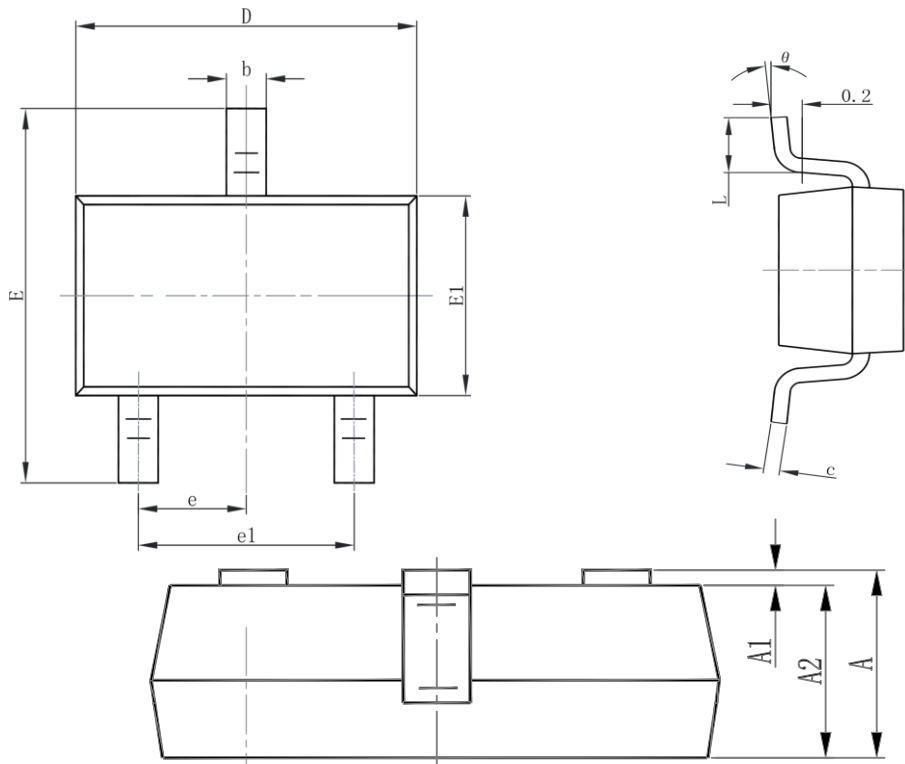
**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature



**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



## Package Information:SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
$\theta$	0°	8°	0°	8°